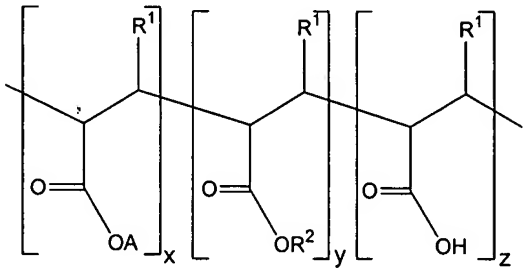
What is claimed is:

1. A ferroelectric film precursor composition, comprising

a ferroelectric polymer or prepolymer,

a casting solvent, and

a leveling agent comprising a (meth)acrylic copolymer represented by formula (I):



wherein

each R^1 is independently a hydrogen or methyl group,

A is $-CR^3R^4R^5$,

wherein

each R^3 is independently a hydrogen, substituted or unsubstituted C_1-C_{20} linear or branched chain alkyl, alkenyl, alkynyl, cycloalkyl, cycloalkenyl, aryl, alkaryl, aralkyl, or heteroaryl moiety, and

each R^4 and R^5 is independently a hydrogen, substituted or unsubstituted C_1-C_{20} linear or branched chain linear or branched chain alkyl, alkenyl, alkynyl, cycloalkyl, cycloalkenyl, aryl, alkaryl, aralkyl, or heteroaryl moiety or R^4 and R^5 together form a C_3-C_8 cycloalkyl group, with the proviso that when R^4 and R^5 are each hydrogen, R^3 is not a linear alkyl group;

R^2 comprises a substituted or unsubstituted C_1-C_{20} linear or branched chain linear or branched chain alkyl, alkenyl, alkynyl, cycloalkyl, cycloalkenyl, aryl, alkaryl, aralkyl, or heteroaryl moiety, wherein the substituents on R^2, R^3, R^4, and R^5 may be halogen, hydroxyl, cyano, nitro, C_1-C_{12} alkyl carboxy ester, acyl, C_1-C_{12} alkoxy, carboxylate, or a mixture comprising one or more of the foregoing groups;

x+y+z = 100 mol%;

x and y are each independently 10 to 70 mol%; and

z is less than or equal to 40 mol%.

2. The composition of claim 1, wherein A has the formula $-CH_2CR^4R^5$, R^4 and R^5 are each independently a C_1-C_{10} linear or branched alkyl, alkenyl, or alkaryl group, or a C_3-C_{10} cycloalkyl or cycloalkenyl group.

3. The composition of Claim 1, wherein R^4 or R^5 or both comprises a site of unsaturation.

4. The composition of claim 1, wherein the ferroelectric polymer comprises a vinylidene fluoride-containing polymer.

5. A process for forming a ferroelectric polymer film, the process comprising:

disposing a casting composition comprising a ferroelectric polymer, a casting solvent, and the leveling agent of claim 1 onto a substrate, and

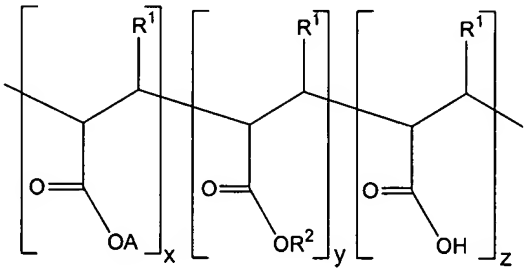
removing at least a portion of the casting solvent composition to produce the ferroelectric polymer film.

6. The process of claim 5, wherein the ferroelectric polymer film has an atomic force microscopy roughness of less than 300 Angstroms, a polydispersity of less than 3, and a Curie transition temperature of greater than 90 degrees Celsius.

7. A ferroelectric polymer film, comprising:

a ferroelectric polymer; and

a leveling agent comprising a (meth)acrylic copolymer represented by formula (I):



wherein

each R^1 is independently a hydrogen or methyl group,

A is $-CR^3R^4R^5$,

wherein

each R^3 is independently a hydrogen, substituted or unsubstituted C_1-C_{20} linear or branched chain alkyl, alkenyl, alkynyl, cycloalkyl, cycloalkenyl, aryl, alkaryl, aralkyl, or heteroaryl moiety, and

each R^4 and R^5 is independently a hydrogen, substituted or unsubstituted C_1-C_{20} linear or branched chain linear or branched chain

alkyl, alkenyl, alkynyl, cycloalkyl, cycloalkenyl, aryl, alkaryl, aralkyl, or heteroaryl moiety or R^4 and R^5 together form a C_3-C_8 cycloalkyl group, with the proviso that when R^4 and R^5 are each hydrogen, R^3 is not a linear alkyl group;

R^2 comprises a substituted or unsubstituted C_1-C_{20} linear or branched chain linear or branched chain alkyl, alkenyl, alkynyl, cycloalkyl, cycloalkenyl, aryl, alkaryl, aralkyl, or heteroaryl moiety, wherein the substituents on R^2, R^3, R^4, and R^5 may be halogen, hydroxyl, cyano, nitro, C_1-C_{12} alkyl carboxy ester, acyl, C_1-C_{12} alkoxy, carboxylate, or a mixture comprising one or more of the foregoing groups;

$x+y+z = 100$ mol%;

x and y are each independently 10 to 70 mol%; and

z is less than or equal to 40 mol%.

8. A data processing device comprising the film of claim 7.

9. The data processing device of claim 8 wherein the film is disposed between a plurality of electrodes.

10. A film stack comprising the ferroelectric polymer film of claim 7 disposed on a substrate.

11. A data processing device comprising the film stack of claim 10.